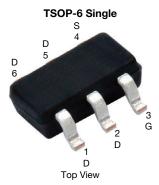
Vishay Siliconix

# Automotive P-Channel 20 V (D-S) 175 °C MOSFET



Marking Code: 9D

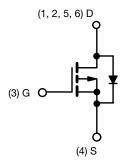
PRODUCT SUMMARY					
V <sub>DS</sub> (V)	-20				
$R_{DS(on)}(\Omega)$ at $V_{GS} = -4.5 \text{ V}$	0.021				
$R_{DS(on)}$ ( $\Omega$ ) at $V_{GS} = -2.5 \text{ V}$	0.032				
I <sub>D</sub> (A)	-8				
Configuration	Single				
Package	TSOP-6				

#### **FEATURES**

- TrenchFET® power MOSFET
- AEC-Q101 qualified c
- 100 % R<sub>q</sub> and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912







P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS	(T <sub>C</sub> = 25 °C, unles	ss otherwise noted	l)		
PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-source voltage	V <sub>DS</sub>	-20	V		
Gate-source voltage	$V_{GS}$	± 12	V		
Continuous drain current	T <sub>C</sub> = 25 °C	I_	-8		
Continuous drain current	T <sub>C</sub> = 125 °C	- I <sub>D</sub>	-7		
Continuous source current (diode conduction	I <sub>S</sub>	-4.5	Α		
Pulsed drain current <sup>a</sup>	I <sub>DM</sub>	-32			
Single pulse avalanche current	L = 0.1 mH	I <sub>AS</sub>	-17		
Single pulse avalanche energy	L = U.1 IIII	E <sub>AS</sub>	14.4	mJ	
Maximum power dissipation <sup>a</sup>	T <sub>C</sub> = 25 °C	P <sub>D</sub>	5	W	
	T <sub>C</sub> = 125 °C		1.67	VV	
Operating junction and storage temperature r	T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C		

THERMAL RESISTANCE RATINGS						
PARAMETER		SYMBOL	LIMIT	UNIT		
Junction-to-ambient	PCB mount b	$R_{thJA}$	110	°C/W		
Junction-to-foot (drain)		$R_{thJF}$	30	C/VV		

#### Notes

- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%$
- b. When mounted on 1" square PCB (FR4 material)
- c. Parametric verification ongoing



# Vishay Siliconix

PARAMETER	SYMBOL	TES	TEST CONDITIONS		TYP.	MAX.	UNIT
Static	- 1	-					
Drain-source breakdown voltage	V <sub>DS</sub>	$V_{GS} = 0$ , $I_D = -250 \mu A$		-20	-	-	V
Gate-source threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250 μA		-1	-1.4	] v
Gate-source leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$		-	± 100	nA
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = -20 V	-	-	-1	
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = -20 V, T <sub>J</sub> = 125 °C	-	-	-50	μΑ
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = -20 V, T <sub>J</sub> = 175 °C	-	-	-150	
On-state drain current a	I <sub>D(on)</sub>	V <sub>GS</sub> = -4.5 V	V <sub>DS</sub> ≤ -5 V	-15	-	-	Α
		V <sub>GS</sub> = -4.5 V	I <sub>D</sub> = -5 A	-	0.016	0.021	Ω
Due in account on atota was into a 2	Б	V <sub>GS</sub> = -4.5 V	I <sub>D</sub> = -5 A, T <sub>J</sub> = 125 °C	-	-	0.034	
Drain-source on-state resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = -4.5 V	I <sub>D</sub> = -5 A, T <sub>J</sub> = 175 °C	-	-	0.034	
		V <sub>GS</sub> = -2.5 V	I <sub>D</sub> = -4 A	-	0.026	0.032	
Forward transconductance <sup>a</sup>	9fs	V <sub>DS</sub> = -10 V, I <sub>D</sub> = -5.6 A		-	24	-	S
Dynamic <sup>b</sup>		•					
Input capacitance	C <sub>iss</sub>			-	2354	3300	
Output capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = -10 V, f = 1 MHz	-	298	420	pF
Reverse transfer capacitance	C <sub>rss</sub>			-	290	405	
Total gate charge <sup>c</sup>	Qg			-	22.7	34	
Gate-source charge <sup>c</sup>	Q <sub>gs</sub>	V <sub>GS</sub> = -4.5 V	$V_{DS} = -10 \text{ V}, I_D = -7.9 \text{ A}$	-	4.5	-	nC
Gate-drain charge <sup>c</sup>	Q <sub>gd</sub>			-	6.4	-	
Gate resistance	$R_g$	f = 1 MHz		2.3	5.9	9.4	Ω
Turn-on delay time <sup>c</sup>	t <sub>d(on)</sub>			-	18	25	
Rise time <sup>c</sup>	t <sub>r</sub>	$V_{DD} = -10 \text{ V}, \text{ R}_{L} = 1.27 \Omega$ $I_{D} \cong -7.9 \text{ A}, \text{ V}_{GEN} = -4.5 \text{ V}, \text{ R}_{g} = 1 \Omega$		-	41	58	- ns
Turn-off delay time <sup>c</sup>	t <sub>d(off)</sub>			-	54	76	
Fall time <sup>c</sup>	t <sub>f</sub>			-	51	71	
Source-Drain Diode Ratings and Char	racteristics <sup>b</sup>						
Pulsed current <sup>a</sup>	I <sub>SM</sub>			-	-	-32	Α
	V <sub>SD</sub>	I <sub>F</sub> = -5 A, V <sub>GS</sub> = 0 V		-	-0.8	-1.2	V

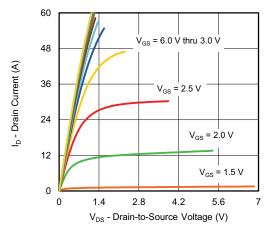
## Notes

- a. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%$
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

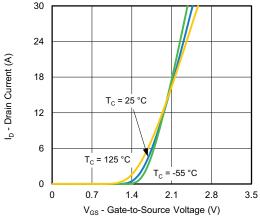
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



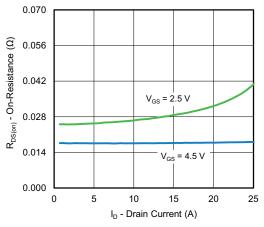
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



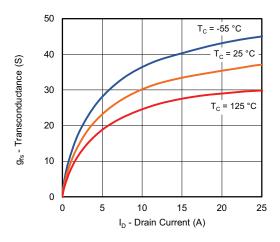
#### **Output Characteristics**



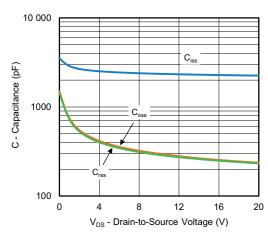
Transfer Characteristics



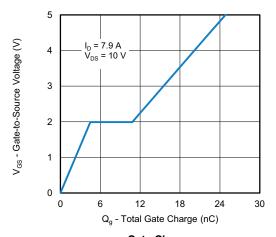
On-Resistance vs. Drain Current



#### Transconductance



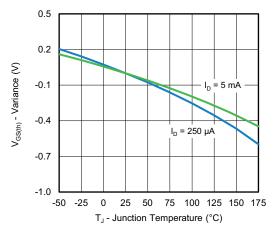
Capacitance



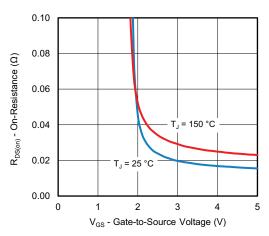
Gate Charge



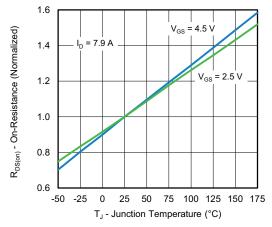
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



#### **Threshold Voltage**



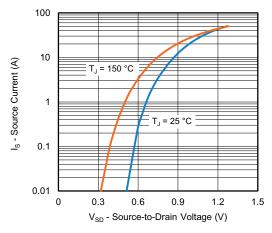
On-Resistance vs. Gate-to-Source Voltage



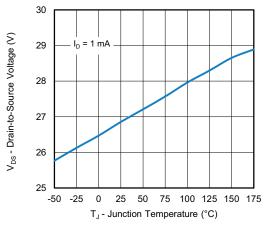
On-Resistance vs. Junction Temperature

#### Note

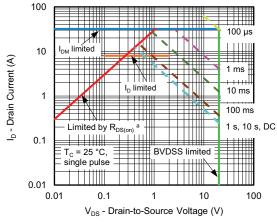
a.  $V_{GS}$  > minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified



**Source Drain Diode Forward Voltage** 



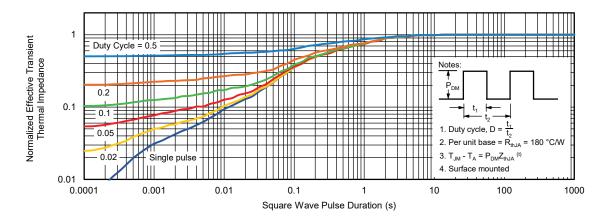
Drain Source Breakdown vs. Junction Temperature



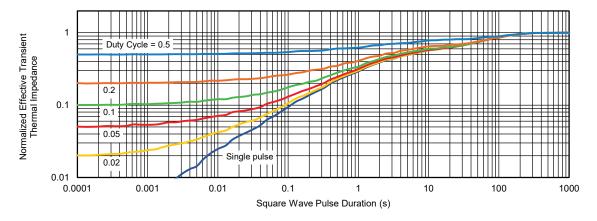
Safe Operating Area

For technical questions, contact: automostechsupport@vishay

## **THERMAL RATINGS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



#### Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

#### Note

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

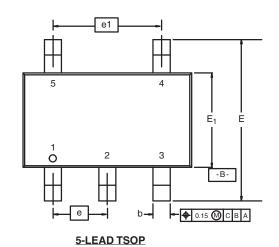
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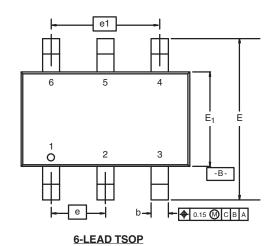


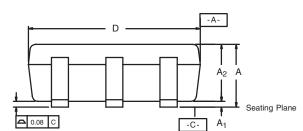


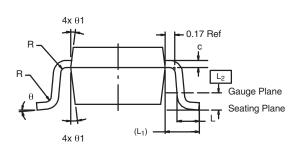
TSOP: 5/6-LEAD

**JEDEC Part Number: MO-193C** 









	MIL	LIMETER	RS	INCHES			
Dim	Min	Nom	Max	Min	Nom	Max	
Α	0.91	-	1.10	0.036	-	0.043	
A <sub>1</sub>	0.01	-	0.10	0.0004	-	0.004	
A <sub>2</sub>	0.90	-	1.00	0.035	0.038	0.039	
b	0.30	0.32	0.45	0.012	0.013	0.018	
С	0.10	0.15	0.20	0.004	0.006	0.008	
D	2.95	3.05	3.10	0.116	0.120	0.122	
E	2.70	2.85	2.98	0.106	0.112	0.117	
E <sub>1</sub>	1.55	1.65	1.70	0.061	0.065	0.067	
е	0.95 BSC			0.0374 BSC			
e <sub>1</sub>	1.80	1.90	2.00	0.071 0.075		0.079	
L	0.32	-	0.50	0.012	-	0.020	
L <sub>1</sub>	0.60 Ref				0.024 Ref		
L <sub>2</sub>	0.25 BSC			0.010 BSC			
R	0.10	-	-	0.004	-	-	
θ	0°	4°	8°	0°	4°	8°	
$\theta_1$	7° Nom			7° Nom			
ECN: C-06593-Rev. I, 18-Dec-06 DWG: 5540							

Document Number: 71200 www.vishay.com 18-Dec-06



# Recommended Land Pattern For TSOP-5L / TSOP-6L



### Note

• All dimensions are in inches (millimeter)

ECN: C22-0860-Rev. B, 24-Oct-2022 DWG: 3010



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